

Product Overview

FGH60T65SQD-F155: 650 V, 60 A Field Stop Trench IGBT

For complete documentation, see the data sheet.

Using novel field stop IGBT technology, ON semiconductor's new series of field stop 4th generation IGBTs offer the optimum performance for solar inverter, UPS, welder, telecom, ESS and PFC applications where low conduction and switching losses are essential.

Features

- Maximum Junction Temperature: $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage: $V_{CE(sat)} = 1.6\text{ V(Typ.) @ } I_C = 60\text{ A}$
- 100% of the Parts Tested for $I_{LM}(1)$
- High Input Impedance
- Fast Switching
- Tighten Parameter Distribution
- RoHS Compliant

Applications

- Solar Inverter, UPS, Welder, Telecom, ESS, PFC

Part Electrical Specifications

Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	I_C Max (A)	$V_{CE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co-Pack aged Diode	Pack age Type
FGH60T65SQD-F155	Pb-free	Active	650	60	1.6	2.3	0.167	0.585	34.6	null	79			333		TO-247-3
	Halide free															

For more information please contact your local sales support at www.onsemi.com.

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